

[METHOD FOR MONITORING OXIDE QUALITY]

Abstract of Disclosure

The present invention utilizes a wafer acceptance testing equipment to fast monitor the quality of a tunnel oxide layer. First, a control gate and a floating gate in a memory cell are electrically connected. Then a plurality of swing time-dependent DC ramping voltages are applied and each corresponding gate leakage current is measured to calculate each corresponding β value. Finally a ratio of each β value is calculated and a β -gate voltage curve is plotted to actually simulate the device failure.